



## High Performance 1:10 Multi-Voltage CMOS Buffer

#### Features

- 10 single-ended outputs Fanout Buffer
- Up to 200MHz output frequency
- Ultra low output additive jitter = 0.05ps (typ.) •
- Selectable reference inputs support Xtal (10~50MHz), singleended and differential
- Low output skew ~ 50ps (typ.)
- Propagation delay ~2ns (typ@3.3V) ٠
- 2.5V / 3.3V operation
- User conf gurable output VDD in different banks: - Mixed 3.3V core/2.5V output operating supply
  - Mixed 3.3V core/1.8V output operating supply
  - Mixed 3.3V core/1.5V output operating supply
  - Mixed 2.5V core/1.8V output operating supply
  - Mixed 2.5V core/1.5V output operating supply
- Industrial temperature range: -40°C to +85°C
- Packaging (Pb-free & Green available):
  - 32-pin TQFN (ZH)

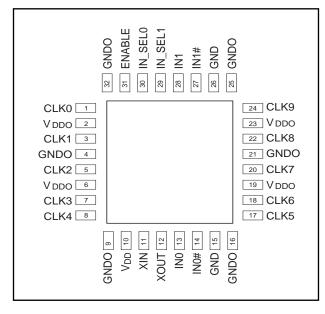
#### **Applications**

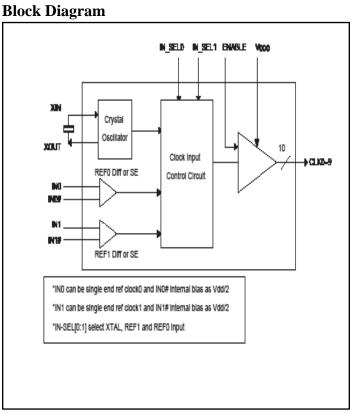
- Networking systems including switches and Routers
- ٠ High frequency backplane based computing and telecom platforms

#### Description

The PI6C49X0210-Ais a high performance multi-voltage 10-outputs CMOS Fanout Buffer with internal Crystal Oscillator. The XTAL range is from 10MHz to 50MHz. The device has a wide range of operating voltages of 2.5V and 3.3V. The device also provides user selectable output VDD option, which provides excellent fexibilities to users. This device is ideal for systems that need to distribute low jitter clock signals to multiple destinations.

### **Pin Configuration**





#### Rev B 16-0143 PI6C49X0210-A





### **Pin Description**

Pin#	Pin Name	Ту	ре	Description
1, 3, 5, 7, 8, 17, 18, 20, 22, 24	CLK0~9	Output		Clock Outputs
2, 6, 19, 23	V <sub>DDO</sub>	Power		Output Power Supplier
15, 26	GND	Power		Output Ground
4, 9, 16, 21, 25, 32	GNDO	Power		Core Ground
10	V <sub>DD</sub>	Power		Core Power Supplier
11	XIN	Input		Crystal interface
12	XOUT	Output		Crystal interface
13	IN0	Input	Pull-down	REF0 Diff or Single End
14	IN0#	Input	Pull-up/ Pull- down	REF0 Diff, When IN0 is single end ref clock0 and IN0# internal bias as Vdd/2
27	IN1#	Input	Pull-up/ Pull- down	REF1 Diff, When IN1 is single end ref clock1 and IN1# internal bias as Vdd/2
28	IN1	Input	Pull-down	REF1 Diff or Single End
30, 29	IN_SEL[0:1]	Input	Pull-down	IN-SEL[0:1] select XTAL, REF1 and REF0 input
31	ENABLE	Input		Active High Output Enable

### **Input Mode Selection Logic**

IN_SEL0	IN_SEL1	Selected Input
1	1	XTAL
0	1	XTAL
1	0	REF1 Diff or Single End
0	0	REF0 Diff or Single End

### **Input/Output Operation State**

Input State	Output State
IN[0:1], IN[0:1]# open	Logic Low
IN[0:1], IN[0:1]# both to ground	Logic Low
IN[0:1]=High, IN[0:1]# =Low	Logic High
IN[0:1]=Low, IN[0:1]# =High	Logic Low

### **Output Mode Selection**

ENABLE	Output CLK0~9
GND	High-impedance
VDD	Enabled





Symbols	Parameters	Test Conditions	Min.	Тур	Max.	Units
V <sub>DD</sub>	Core Supply Voltage		3.135	3.3	3.465	V
V <sub>DDO</sub>	Output Supply Voltage		3.135	3.3	3.465	V
I <sub>DD</sub>	Power Supply Current	ENABLE = '0'			32	mA
I <sub>DDO</sub>	Output Supply Current	ENABLE = '0'			1	mA

#### Power Supply DC Characteristics ( $V_{DD}/V_{DDO} = 3.3V \pm 5\%$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

#### **Power Supply DC Characteristics** ( $V_{DD}/V_{DDO} = 2.5V \pm 5\%$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

11.7		, 11	/			
Symbols	Parameters	Test Conditions	Min.	Тур	Max.	Units
V <sub>DD</sub>	Core Supply Voltage		2.375	2.5	2.625	V
V <sub>DDO</sub>	Output Supply Voltage		2.375	2.5	2.625	V
I <sub>DD</sub>	Power Supply Current	ENABLE = '0'			15	mA
I <sub>DDO</sub>	Output Supply Current	ENABLE = '0'			0.7	mA

#### **Power Supply DC Characteristics** ( $V_{DD} = 3.3V \pm 5\%$ , $V_{DDO} = 2.5V \pm 5\%$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

Symbols	Parameters	Test Conditions	Min.	Тур	Max.	Units
V <sub>DD</sub>	Core Supply Voltage		3.135	3.3	3.465	V
V <sub>DDO</sub>	Output Supply Voltage		2.375	2.5	2.625	V
I <sub>DD</sub>	Power Supply Current	ENABLE = '0'			29	mA
I <sub>DDO</sub>	Output Supply Current	ENABLE = '0'			0.6	mA

#### **Power Supply DC Characteristics** ( $V_{DD} = 3.3V \pm 5\%$ , $V_{DDO} = 1.8V \pm 0.2V$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

Symbols	Parameters	Test Conditions	Min.	Тур	Max.	Units
V <sub>DD</sub>	Core Supply Voltage		3.135	3.3	3.465	V
V <sub>DDO</sub>	Output Supply Voltage		1.6	1.8	2.0	V
I <sub>DD</sub>	Power Supply Current	ENABLE = '0'			29	mA
I <sub>DDO</sub>	Output Supply Current	ENABLE = '0'			0.4	mA

#### **Power Supply DC Characteristics** ( $V_{DD} = 3.3V \pm 5\%$ , $V_{DDO} = 1.5V \pm 0.15V$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

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I <sub>DD</sub>	Power Supply Current	ENABLE = '0'			29	mA
I <sub>DDO</sub>	Output Supply Current	ENABLE = '0'			0.3	mA





Symbols	Parameters	Test Conditions	Min.	Тур	Max.	Units
V <sub>DD</sub>	Core Supply Voltage		2.375	2.5	2.625	V
V <sub>DDO</sub>	Output Supply Voltage		1.6	1.8	2.0	V
I <sub>DD</sub>	Power Supply Current	ENABLE = '0'			13	mA
I <sub>DDO</sub>	Output Supply Current	ENABLE = '0'			0.4	mA

#### **Power Supply DC Characteristics** $(V_{DD} = 2.5V + 5\%, V_{DDO} = 1.8V + 0.2V$ T<sub>4</sub> = -40°C to 85°C)

### Power Supply DC Characteristics ( $V_{DD} = 2.5V \pm 5\%$ , $V_{DDO} = 1.5V \pm 0.15V$ , $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

Symbols	Parameters	Test Conditions	Min.	Тур	Max.	Units
V <sub>DD</sub>	Core Supply Voltage		2.375	2.5	2.625	V
V <sub>DDO</sub>	Output Supply Voltage		1.35	1.5	1.65	V
I <sub>DD</sub>	Power Supply Current	ENABLE = '0'			13	mA
I <sub>DDO</sub>	Output Supply Current	ENABLE = '0'			0.3	mA





Symbols	Parameters	Test Conditions	Min.	Тур	Max.	Units
V	Lugart III als Malta an	$V_{DD}=3.3V\pm5\%$	2		V <sub>DD</sub> + 0.3	V
VIH	Input High Voltage	$V_{DD}=2.5V\pm5\%$	1.7		V <sub>DD</sub> + 0.3	V
<sup>7</sup> пн <sup>7</sup> п. <sup>7</sup> он	Lucut I and Valta as	$V_{DD}=3.3V\pm5\%$	-0.3		0.8	V
VIL	Input Low Voltage	$V_{DD}=2.5V\pm5\%$	-0.3		0.7	V
		$V_{DDO} = 3.3V \pm 5\%^{(1)}$	2.6			V
		$V_{DDO}=2.5V\pm5\%$	2.0			V
	Output High Voltage (I <sub>OH</sub> = -8mA)	$\begin{array}{c} V_{DDO} = 1.8V \pm \\ 0.2V^{(1)} \end{array}$	1.5			v
V		$\frac{V_{DDO} = 1.5V \pm}{0.15V^{(1)}}$	1.0			v
VOH		$V_{DDO} = 3.3V \pm 5\%^{(1)}$	3.0			
		$V_{DDO}=2.5V\pm5\%$	2.0			
	Output High Voltage (I <sub>OH</sub> = -12mA)	$\frac{V_{DDO}=1.8V\pm}{0.2V^{(1)}}$	1.5			
		$\frac{V_{DDO} = 1.5V \pm }{0.15V^{(1)}}$	1.0			
		$V_{DDO} = 3.3V \pm 5\%$ <sup>(1)</sup>			0.5	V
		$V_{DDO}=2.5V\pm5\%$			0.5	V
	Output Low Voltage (I <sub>OL</sub> = 8mA)	$\underset{(1)}{V_{DDO}}=1.8V\pm0.2V$			0.4	v
X7		$V_{DDO} = 1.5V \pm 0.15V$			0.35	v
VOL		$V_{DDO} = 3.3V \pm 5\%$ <sup>(1)</sup>			0.25	V
		$V_{DDO}=2.5V\pm5\%$			0.25	V
	Output Low Voltage (I <sub>OL</sub> = 12mA)	$\frac{V_{DDO}}{(1)} = 1.8V \pm 0.2V$			0.3	v
		$V_{DDO} = 1.5V \pm 0.15V$			0.35	v
		$V_{DDO} = 3.3V \pm 5\%$ <sup>(1)</sup>		9		
		$V_{DDO}=2.5V\pm~5\%$		10		
R <sub>OUT</sub>	Output Impedence	$V_{DDO} = 1.8V \pm 0.2V$		20		
		$\frac{V_{DDO}=1.5V\pm}{0.15V}$		30		

# Single-Ended DC Characteristics ( $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

Notes:

1. Outputs terminated with 50 to  $V_{DDO}$  /2. See Parameter Measurement section, "Load Test Circuit" diagrams.





Symbols	Para	meters	Test Conditions	Min.	Тур	Max.	Units	
I <sub>IH</sub>	Input High Current	IN[0:1], IN[0:1]#	$V_{DD} = V_{IN} = 3.465 V$ or 2.625 V			100	uA	
т	Input Low	IN[0:1]	$V_{DD} = 3.465 V \text{ or}$ 2.625 V $V_{IN} = 0 V$	-1			uA	
п	Current	IN[0:1]#	$V_{DD} = 3.465 V \text{ or}$ 2.625 V $V_{IN} = 0 V$	-50			uA	
V	Deals to Deals I	nput Voltage <sup>(1)</sup>	$V_{DD} = 3.3 V$	0.25		1.3	v	
V <sub>PP</sub> I	Peak-to-Peak I	nput voltage V	$V_{DD} = 2.5 V$	0.25		1.3	V	
V	Common Mod	e Input Voltage	$V_{DD} = 3.3V$	0.5		V <sub>DD</sub> -1.35V	V	
V <sub>CMR</sub>	(1,2)		$V_{DD} = 2.5 V$	0.5		V <sub>DD</sub> -0.85V	V	

# **Differential input DC Characteristics** ( $T_A = -40^{\circ}C$ to $85^{\circ}C$ )

Notes:

1.  $V_{IL}$  should not be less than -0.3V.

2. Common mode voltage is defined as  $V_{IH}$ .





3.3V Absolute Maximum Ratings (Above which the useful life may be impaired. For user guidelines only, not tested.)

#### Note:

Storage Temperature	$-65^{\circ}C \text{ to } +150^{\circ}C$
V <sub>DD</sub> , V <sub>DDO</sub> Voltage	-0.5V to +3.6V
Output Voltage (max. 4.6V)	–0.5V to V <sub>DD</sub> +0.5V
Input Voltage (max 4.6V)	$-0.5V$ to $V_{DD}+0.5V$
Junction Temperature	125°C max

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### AC Characteristics (Over Operating Range: V-

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2.5V Absolute Maximum Ratings (Above which the useful life may be impaired. For user guidelines only, not tested.)

#### Note:

Storage Temperature65°C to +150°C
V <sub>DD</sub> , V <sub>DDO</sub> Voltage0.5V to +3.6V
Output Voltage (max. 4.6V)0.5V to V <sub>DD</sub> +0.5V
Input Voltage (max 4.6V)0.5V to V <sub>DD</sub> +0.5V
Junction Temperature

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

AC Characteristics (Over Operating Range:  $V_{DD}/V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^{\circ}$  to  $85^{\circ}$ C)

Parameters	De	scription	Test Conditions <sup>(1)</sup>	Min.	Тур	Max.	Units
		Using External Crystal		10		50	
f <sub>MAX</sub>	Output Frequency	Using External Clock Source <sup>(2)</sup>		DC		200	MHz
odc	Output Duty Cycle		125MHz	45		55	%
t <sub>sk(o)</sub>	Output Skew <sup>(3)</sup>					80	ps
t <sub>jit(Ø)</sub>	RMS Phase Jitter (I	Random)	25MHz @ (Integra- tion Range: 100Hz- 1MHz)		0.2		ps
tjit(additive)	Additive RMS Pha	e Jitter (Random)	125MHz @ (Integra- tion Range: 12kHz- 20MHz)		0.05		ps
$t_{\rm R}/t_{\rm F}$	Output Rise/Fall Ti	me	20% to 80%	200		800	ps
t <sub>EN</sub>	Output Enable Time	e ENABLE				5	cycles
t <sub>DIS</sub>	Output Disable Tim	e ENABLE				5	cycles
MUX <sub>isolation</sub>	MUX Isolation	•	155.52MHz		63		dB

Notes:

1. Unless noted otherwise, all parameters are tested with xtal @  $f \le Fxtal_max$ ; outputs are terminated @ 50 to  $V_{DDO}/2$ , see waveforms.

2. Diff external clock source is driving IN0/IN0# and IN1/IN1# input. IN0/IN1 can be single end ref clock when IN0# /IN1# set as VDD/2

3. Identical conditions: loading, transitions, supply voltage, temperature, package type and speed grade.





Parameters	De	scription	Test Conditions <sup>(1)</sup>	Min.	Тур	Max.	Units
		Using External Crystal		10		50	
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$t_{\rm R}/t_{\rm F}$	Output Rise/Fall Ti	me	20% to 80%	200		800	ps
t <sub>EN</sub>	Output Enable Time	e ENABLE				5	cycles
t <sub>DIS</sub>	Output Disable Tim	e ENABLE				5	cycles
MUX <sub>isolation</sub>	MUX Isolation	•	155.52MHz		62		dB

#### AC Characteristics (Over Operating Range: $V_{DD} = 3.3V \pm 5\%$ , $V_{DDO} = 2.5V \pm 5\%$ , $T_A = -40^{\circ}$ to $85^{\circ}$ C)

Notes:

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f <sub>MAX</sub>	Output Frequency	Using External Clock Source <sup>(2)</sup>		DC		200	MHz
odc	Output Duty Cycle		125MHz	45		55	%
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tjit(additive)	Additive RMS Phas	e Jitter (Random)	125MHz @ (Integra- tion Range: 12kHz- 20MHz)		0.05		ps
$t_{\rm R}/t_{\rm F}$	Output Rise/Fall Ti	me	20% to 80%	200		900	ps
t <sub>EN</sub>	Output Enable Time	e ENABLE				5	cycles
t <sub>DIS</sub>	Output Disable Tim	e ENABLE				5	cycles
MUX <sub>isolation</sub>	MUX Isolation	• 	155.52MHz		58		dB

#### AC Characteristics (Over Operating Range: $V_{DD} = 3.3V \pm 5\%$ , $V_{DDO} = 1.8V \pm 0.2V$ , $T_A = -40^{\circ}$ to $85^{\circ}$ C)

Notes:

1. Unless noted otherwise, all parameters are tested with xtal @  $f \ll Fxtal_max$ ; outputs are terminated @ 50 to  $V_{DDO}/2$ , see waveforms.

2. Diff external clock source is driving IN0/IN0# and IN1/IN1# input. IN0/IN1 can be single end ref clock when IN0# /IN1# set as VDD/2

3. Identical conditions: loading, transitions, supply voltage, temperature, package type and speed grade.





### AC Characteristics (Over Operating Range: $V_{DD} = 3.3V \pm 5\%$ , $V_{DDO} = 1.5V \pm 0.15V$ , $T_A = -40^{\circ}$ to $85^{\circ}$ C)

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t <sub>sk(o)</sub>	Output Skew <sup>(3)</sup>					80	ps
t <sub>jit(Ø)</sub>	RMS Phase Jitter (I	Random)	25MHz @ (Integra- tion Range: 100Hz- 1MHz)		0.15		ps
tjit(additive)	Additive RMS Phas	e Jitter (Random)	125MHz @ (Integra- tion Range: 12kHz- 20MHz)		0.12		ps
t <sub>R</sub> /t <sub>F</sub>	Output Rise/Fall Ti	me	20% to 80%	200		900	ps
t <sub>EN</sub>	Output Enable Time	e ENABLE				5	cycles
t <sub>DIS</sub>	Output Disable Tim	e ENABLE				5	cycles
MUX <sub>isolation</sub>	MUX Isolation		155.52MHz		59		dB

#### AC Characteristics (Over Operating Range: $V_{DD} = 2.5V \pm 5\%$ , $V_{DDO} = 1.8V \pm 0.2V$ , $T_A = -40^{\circ}$ to $85^{\circ}$ C)

Notes:

1. Unless noted otherwise, all parameters are tested with xtal @  $f \le Fxtal_max$ ; outputs are terminated @ 50 to  $V_{DDO}/2$ , see waveforms.

2. Diff external clock source is driving IN0/IN0# and IN1/IN1# input. IN0/IN1 can be single end ref clock when IN0# /IN1# set as  $V_{DD}/2$ 

3. Identical conditions: loading, transitions, supply voltage, temperature, package type and speed grade.





Parameters	De	scription	Test Conditions <sup>(1)</sup>	Min.	Тур	Max.	Units
		Using External Crystal		10		50	
f <sub>MAX</sub>	Output Frequency	Using External Clock Source <sup>(2)</sup>		DC		200	MHz
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t <sub>jit(Ø)</sub>	RMS Phase Jitter (I	Random)	25MHz @ (Integra- tion Range: 100Hz- 1MHz)		0.15		ps
tjit(additive)	Additive RMS Phas	e Jitter (Random)	125MHz @ (Integra- tion Range: 12kHz- 20MHz)		0.05		ps
t <sub>R</sub> /t <sub>F</sub>	Output Rise/Fall Ti	me	20% to 80%	200		900	ps
t <sub>EN</sub>	Output Enable Time	ENABLE				5	cycles
t <sub>DIS</sub>	Output Disable Tim	e ENABLE				5	cycles
MUX <sub>isolation</sub>	MUX Isolation	•	155.52MHz		55		dB

#### AC Characteristics (Over Operating Range: $V_{DD} = 2.5V \pm 5\%$ , $V_{DDO} = 1.5V \pm 0.15V$ , $T_A = -40^{\circ}$ to $85^{\circ}$ C)

1. Unless noted otherwise, all parameters are tested with xtal @  $f \ll Fxtal_max$ ; outputs are terminated @ 50 to  $V_{DDO}/2$ , see waveforms.

2. Diff external clock source is driving IN0/IN0# and IN1/IN1# input. IN0/IN1 can be single end ref clock when IN0# /IN1# set as VDD/2

3. Identical conditions: loading, transitions, supply voltage, temperature, package type and speed grade.

4. These parameters are guaranteed, but not tested. Max delay is 4 cycles. Min. setup time = 3ns.

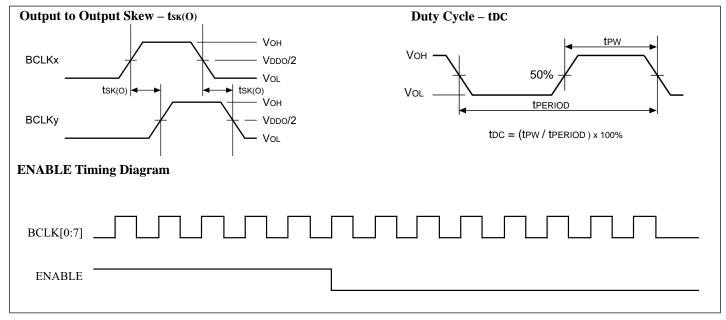
#### **Crystal Oscillator Characteristics**

Parameters	Description	Min	Тур	Max.	Units
OSCMODE	Mode of Oscillation	Fundamental			
FREQ	Frequency	10	25	50	MHz
C <sub>ON-CHIP</sub>	On chip Load Capacitance		12		pF

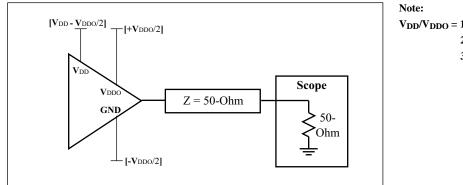




#### Waveforms



#### **AC Test Circuit Load**



 $V_{DD}/V_{DDO} = 1.8V \pm 0.2V,$  $2.5V \pm 5\%$ ,  $3.3V \pm 5\%$ 

Crystal Characteristic (link to "http://www.pericom.com/products/timing/crystals/index.php" for more detailed and different size crystal specifications)

Parameters	Description	Min	Тур	Max.	Units
OSCMODE	Mode of Oscillation	]	Fundamental		
FREQ	Frequency	10	25	50	MHz
ESR <sup>(1)</sup>	Equivalent Series Resistance	30		50	Ohm
CLOAD	Load Capacitance		18		pF
CSHUNT	Shunt Capacitance			7	pF
DRIVE level				1	mW

Note: 1. ESR value is dependent upon frequency of oscillation

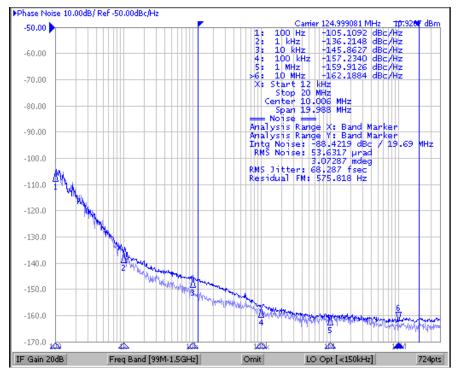




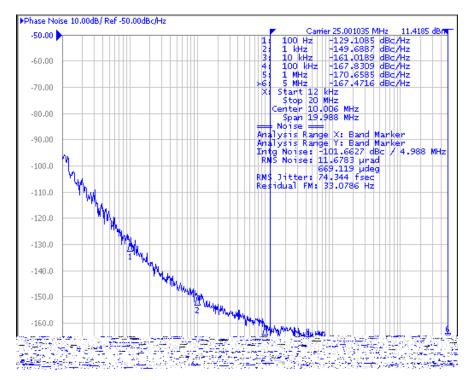
#### **Phase Noise and Additive Jitter**

Output phase noise (Dark Blue) vs Input Phase noise (light blue)

Additive jitter is calculated at ~47fs RMS (12kHz to 20MHz). Additive jitter =  $\sqrt{(\text{Output jitter}^2 - \text{Input jitter}^2)}$ 



### **Oscillator Phase Jitter**



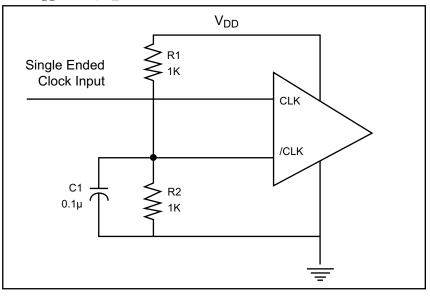


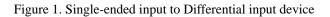


### Application Information

#### Wiring the differential input to accept single ended levels

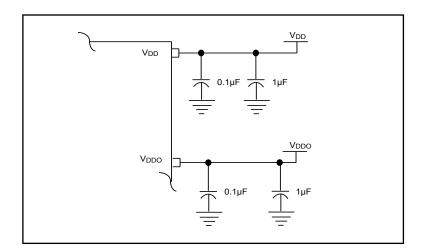
Figure 1 shows how the differential input can be wired to accept single ended levels. The reference voltage  $V_{REF} = V_{DD}/2$  is generated by the bias resistors R1, R2 and C1. This bias circuit should be located as close as possible to the input pin. The ratio of R1 and R2 might need to be adjusted to postion the V\_REF in the center of the input voltage swing. For example, if the input clock swing is only 2.5V and  $V_{DD} = 3.3V$ ,  $V_{REF}$  should be 1.25V and R1/R2 = 0.609.





#### **Power Supply Filtering Techniques**

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. All power pins should be individually connected to the power supply plane through vias, 0.1µF and 1µF bypass capacitors should be used for each pin.

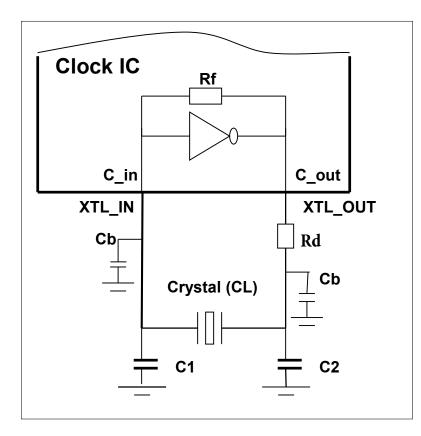






#### **Application Notes**

### Clock IC Crystal loading cap. design guide



CL = crystal spec. loading cap.

 $C_in/out = (3 \sim 5pF)$  of IC pin cap.

 $Cb = PCB trace (2 \sim 4pF)$ 

C1,C2 = load cap. of design

Rd = 50 to 1000hm drive level limit (Optimized for 25MHz 18pf XTAL without Rd)

Design guide: C1=C2=2 \*CL - (Cb +C\_in/out) to meet target +/-ppm < 20 ppm

Example1: Select CL=18 pF crystal, C1=C2=2\*(18pF) - (4pF+5pF)=27pF, check datasheet too

Example2: For higher frequency crystal (=>20MHz), can use formula C1=C2=2\*(CL-6), can do fine tune of C1, C2 for more accurate ppm if necessary

#### **Thermal Information**

Symbol	Description	Condition	
$\Theta_{JA}$	Junction-to-ambient thermal resistance	Still air	44.7 °C/W
$\Theta_{\rm JC}$	Junction-to-case thermal resistance		21.7 °C/W





### **Crystal Input Drive Level vs Series Resistor Value**



Note:

- 1. Drive Level above is with regards to VDD = 3.3V. If VDD= 2.5V, drive level is 25% lower
- 2. For Rd= 0 Ohm, Drive Level =  $310 \ \mu W$





### **Ordering Information**<sup>(1,2,3)</sup>

Ordering Code	Package Code	Package Description
PI6C49X0210-AZHIE	ZH	Pb-Free and Green 32-pin TQFN
PI6C49X0210-AZHIEX	ZH	Pb-Free and Green 32-pin TQFN, Tape & Reel

Notes:

Thermal characteristics can be found on the company web site at www.pericom.com/packaging/ 1.

2.





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